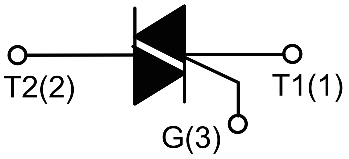
DESCRIPTION:

With high ability to withstand the shock loading of large current, T2535-800G series triacs provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, 3 quadrants products especially recommended for use on inductive load.

TO-263

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	25	A
V_{DRM} /V_{RRM}	600/800/1200/1600	V



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	℃
Operating junction temperature range		T_j	-40-125	℃
Repetitive peak off-state voltage (T_j=25℃)		V_{DRM}	600/800/1200/1600	V
Repetitive peak reverse voltage (T_j=25℃)		V_{RRM}	600/800/1200/1600	V
RMS on-state current	TO-263 (T_C=75℃)	$I_{T(RMS)}$	25	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)		I_{TSM}	250	A
I^2t value for fusing (tp=10ms)		I^2t	340	A^2s
Critical rate of rise of on-state current (I_G =2×I_{GT})		dI/dt	50	A/μs
Peak gate current		I_{GM}	4	A
Average gate power dissipation		$P_{G(AV)}$	1	W
Peak gate power		P_{GM}	10	W

ELECTRICAL CHARACTERISTICS (T_j=25℃ unless otherwise specified)

V_{DRM} /V_{RRM}: 600/800V

Symbol	Test Condition	Quadrant		JST24-600/800V		Unit
				BW	**CW**	
I_{GT}	V_D =12V R_L =33Ω	Ⅰ-Ⅱ-Ⅲ	MAX	50	35	mA
V_{GT}		Ⅰ-Ⅱ-Ⅲ	MAX	1.3		V
V_{GD}	V_D =V_{DRM} T_j =125℃ R_L =3.3KΩ	Ⅰ-Ⅱ-Ⅲ	MIN	0.2		V
I_L	I_G =1.2I_{GT}	Ⅰ-Ⅲ	MAX	80	70	mA
		Ⅱ		100	80	
I_H	I_T =100mA		MAX	75	50	mA
dV/dt	V_D=2/3V_{DRM} Gate Open T_j =125℃		MIN	1000	500	V/μs

V_{DRM} /V_{RRM}: 1200/1600V

Symbol	Test Condition	Quadrant		JST24-1200V/1600V		Unit
				BW	**CW**	
I_{GT}	V_D =12V R_L=33Ω	Ⅰ-Ⅱ-Ⅲ	MAX	50	35	mA
V_{GT}		Ⅰ-Ⅱ-Ⅲ	MAX	1.5		V
V_{GD}	V_D =V_{DRM} T_j =125℃ R_L =3.3KΩ	Ⅰ-Ⅱ-Ⅲ	MIN	0.2		V
I_L	I_G =1.2I_{GT}	Ⅰ-Ⅲ	MAX	90	70	mA
		Ⅱ		100	80	
I_H	I_T =100mA		MAX	80	60	mA
dV/dt	V_D=2/3V_{DRM} Gate Open T_j=125℃		MIN	1500	1000	V/μs

V_{DRM} /V_{RRM}: 600/800V

Symbol	Test Condition	Quadrant		JST24-600/800V		Unit
				B	**C**	
I_{GT}	V_D =12V R_L =33Ω	Ⅰ-Ⅱ-Ⅲ	MAX	50	25	mA
		Ⅳ		70	50	
V_{GT}		ALL	MAX	1.3		V
V_{GD}	V_D =V_{DRM} T_j =125℃ R_L =3.3KΩ	ALL	MIN	0.2		V

I_L	$I_G=1.2I_{GT}$	Ⅰ -Ⅲ-Ⅳ	MAX	80	70	mA
		Ⅱ	MAX	100	90	
I_H	$I_T=100mA$		MAX	75	60	mA
dV/dt	V_D=2/3V_{DRM} Gate Open T_j=125℃		MIN	500	200	V/μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	I_{TM} =35A tp=380μs	T_j=25℃	1.5	V
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	T_j=25℃	5	μA
I_{RRM}		T_j=125℃	3	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-263	1.3	℃/W
$R_{th(j-a)}$	junction to ambient		45	

FIG.1: Maximum power dissipation versus RMS on-state current

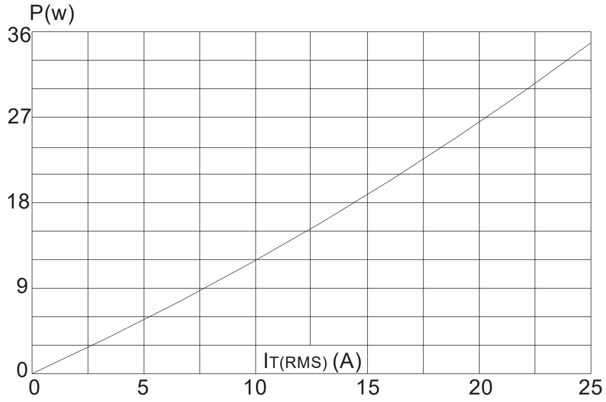


FIG.2: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness:35μm)(full cycle)

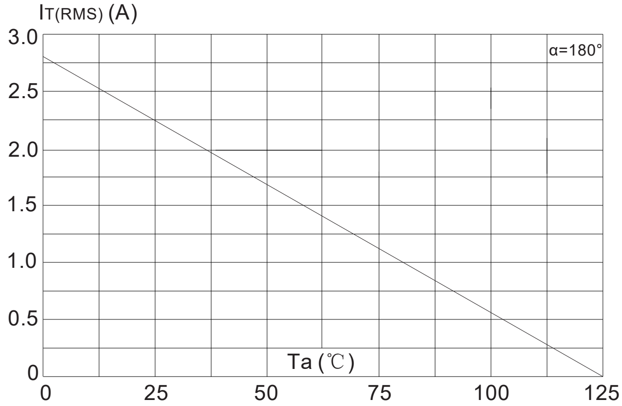


FIG.3: Surge peak on-state current versus number of cycles

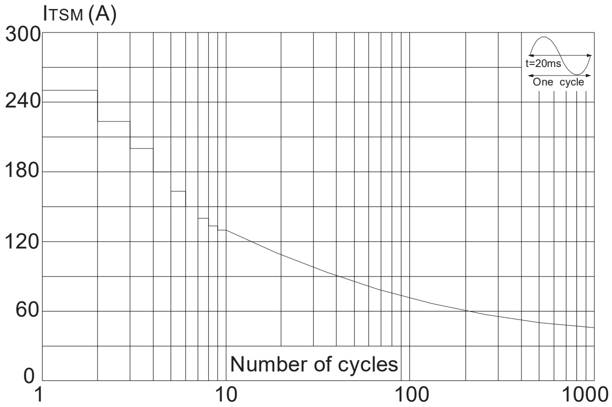


FIG.4: On-state characteristics (maximum values)

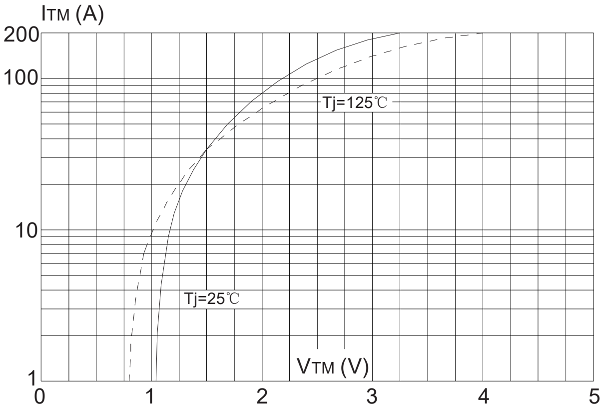


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms, and corresponging value of I^2t (dI/dt < 50A/μs)

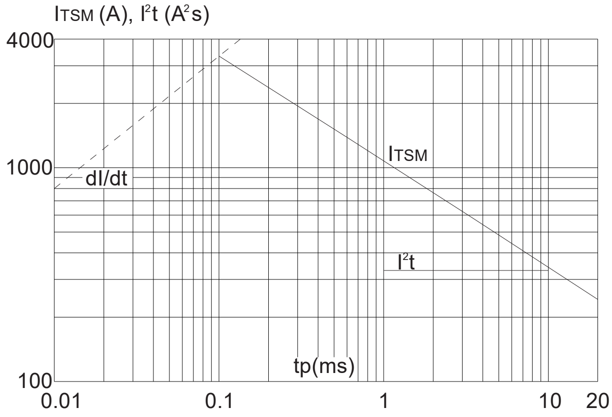
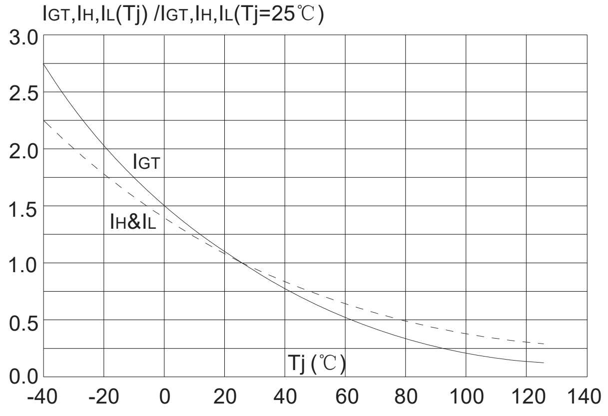


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150℃
	-Temperature Max($T_{s(max)}$)	+200℃
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L)to peak)		3℃/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3℃/sec. Max
Reflow	-Temperature(T_L) (Liquidus)	+217℃
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)℃
Time within 5℃of actual Peak Temp (t_p)		20-40secs.
Ramp-down Rate		6℃/sec. Max
Time 25℃ to Peak Temp (T_P)		8 min. Max
Do not exceed		+260℃